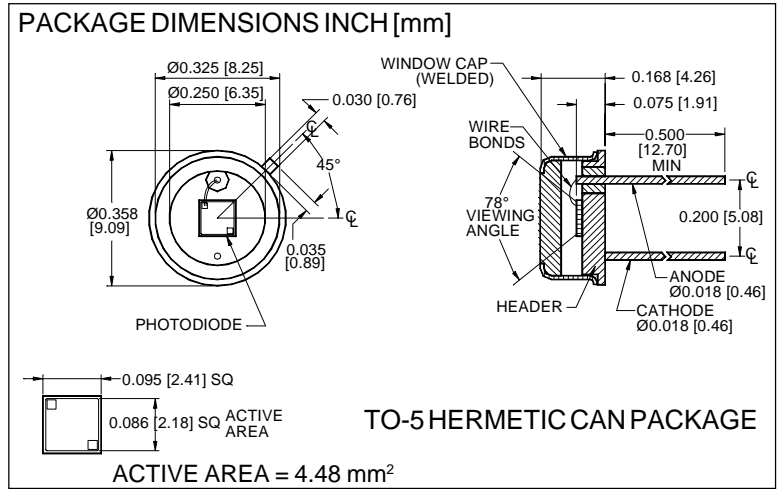


# PHOTONIC DETECTORS INC.

## Silicon Photodiode, Blue Enhanced Photoconductive Type PDB-C105



### FEATURES

- High speed
- Low capacitance
- Blue enhanced
- Low dark current

### DESCRIPTION

The **PDB-C105** is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive applications. Packaged in a hermetic TO-5 metal can with a flat window.

### APPLICATIONS

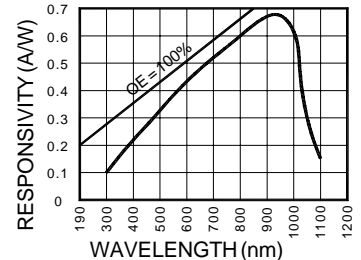
- Instrumentation
- Laser detection
- Medical sensor
- Industrial control

### ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V <sub>BR</sub>	Reverse Voltage		100	V
T <sub>STG</sub>	Storage Temperature	-55	+150	°C
T <sub>O</sub>	Operating Temperature Range	-40	+125	°C
T <sub>S</sub>	Soldering Temperature*		+240	°C
I <sub>L</sub>	Light Current		0.5	mA

\*1/16 inch from case for 3 secs max

### SPECTRAL RESPONSE



### ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>SC</sub>	Short Circuit Current	H = 100 fc, 2850 K	40	56		μA
I <sub>D</sub>	Dark Current	H = 0, V <sub>R</sub> = 10 V		1.0	5.0	nA
R <sub>SH</sub>	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	.5	2.0		GΩ
TC <sub>RSH</sub>	RSH Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		% / °C
C <sub>J</sub>	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V**		11		pF
λ <sub>range</sub>	Spectral Application Range	Spot Scan	350		1100	nm
λ <sub>p</sub>	Spectral Response - Peak	Spot Scan		950		nm
V <sub>BR</sub>	Breakdown Voltage	I = 10 μA	100	125		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		2.0x10 <sup>-14</sup>		W/√Hz
tr	Response Time	RL = 1 KΩ V <sub>R</sub> = 50 V		12		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.\*\*f = 1 MHz

[FORM NO. 100-PDB-C105 REV B]